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EDUCATION

- 2014** **Master 2 (Msc) in Theoretical Physics** (magna cum laude) Hebrew University of Jerusalem, Israel
- 1996** **Master 2 (DESS) in Management (MBA)** Pantheon-Sorbonne University School of Management, Paris, France
- 1993** **Master 2 (DEA) in Microelectronics**, (magna cum laude, major), Paris 7 University, France
- 1992** **Master 2 (DEA) Applied Physics**, (cum laude), Bordeaux I University, France
Engineering Diploma (Electrical engineering and Telecom), ENSEIRB-MATMECA School of Engineering, France
"Ecole Nationale Supérieure d'Electronique, d'Informatique et de Radiocommunications de Bordeaux"
- 1989** **DEUG A (BSc 2 years program) Physics and Mathematics** (magna cum laude), Nice University, France

ARTICLES

[Leading anomalies, the drift Hamiltonian and the relativistic two-body system](#)

BM Nabet, B Kol - arXiv preprint arXiv:1408.2628, 2014 - arxiv.org

Abstract: We suggest to solve for the motion of the two body problem in General Relativity by identifying the leading violation of conserved quantities, referred to as (relativistic) anomalies, ordered by the post-Newtonian order at which they appear. This differs from the ...

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<https://arxiv.org/abs/1408.2628>

[Laser-emitting component having an injection zone of limited width](#)

B Nabet, JC Bouley, N Bouadma - US Patent 5,818,863, 1998 - Google Patents

A vertical-cavity surface-emitting laser component operating at a wavelength lying in the range 1.3 μm to 1.55 μm , the component comprising a layer of active material having an injection zone of width that is smaller than the width of the component, said zone emitting ...

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<https://patents.google.com/patent/US5818863A/en>

[Reflectivity in Bragg Mirrors of AlGaAsSb/AlAsSb on InP](#)

JC Harmand, B Nabet, E Laureto... - ... : Ciências Exatas e ..., 2003 - ingentaconnect.com

The reflectivity of a Bragg mirror composed by materials of the antimony family (AlGaAsSb/AlAsSb), doped with tellurium, is analyzed in this work. The sample was prepared by molecular beam epitaxy (MBE) and the reflectivity was measured by Fourier ...

<http://www.ingentaconnect.com/content/doi/16765451/2003/00000024/00000001/art00007>

Electrical and optical characteristics of n-type-doped distributed Bragg mirrors on InP

[IFL Dias](#), [B Nabet](#), A Kohl, JL Benchimol... - IEEE Photonics ..., 1998 - ieeexplore.ieee.org

The development of high reflectivity and low electrical resistivity Bragg mirrors is crucial for the emergence of 1.55- μm vertical-cavity surface-emitting lasers (VCSEL's). Here, we report on three different n-type-doped semiconductor Bragg mirrors which are all lattice ...

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<http://ieeexplore.ieee.org/abstract/document/681476/>

High reflectivity, low resistance Te doped AlGaAsSb/AlAsSb Bragg mirror

[IFL Dias](#), [B Nabet](#), A Kohl, JC Harmand - Electronics Letters, 1997 - ieeexplore.ieee.org

The authors report a high quality n-type Te-doped AlGaAsSb/AlAsSb Bragg mirror lattice matched to InP grown by molecular beam epitaxy. A 99.8% reflectivity with a 190 nm stopband width centred at 1.51- μm is obtained. An average voltage drop of 44 mV per ...

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